

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hisao HAYASHI et al)

Group Art Unit: 2811

Appln. No.: 09/772,986 ✓ )

Examiner: Tran, Thien F. )

Filed: January 31, 2001 )

THIN FILM SEMICONDUCTOR DEVICE, DISPLAY )  
DEVICE USING SUCH THIN FILM SEMICONDUCTOR )  
DEVICE AND MANUFACTURING METHOD THEREOF )BOX NON-FEE AMENDMENT  
Commissioner of Patents  
Washington, D.C. 20231RECEIVED  
AUG - 9 2002  
TECHNOLOGY CENTER 2800AMENDMENT UNDER 37 C.F.R. § 1.111

Sir:

Responsive to the non-final Office Action dated May 8, 2002, (Paper No. 7), please amend the above-referenced application as follows.

IN THE CLAIMS:

Please rewrite claim 8 as set forth below in clean form. Additionally, in accordance with 37 CFR 1.121(c)(1)(ii), amended claim 8 is set forth in a marked-up version in the pages attached to this Amendment.

8. (Amended) The display device according to Claim 5, wherein said gate electrode has a multi-layer structure stacked with an upper layer having comparatively low heat conductivity and high electric resistance, and a lower layer having comparatively high heat conductivity and low electric resistance.

REMARKS

Applicant is in receipt of the detailed Office Action mailed May 8, 2002. Claims 1-12 are pending and Claims 9-12 have been withdrawn from consideration. Applicant requests reconsideration of the remaining claims in view of the following remarks.